ML67Q5260

DFT Based Fingerprint Authentication LSI

GENERAL DESCRIPTION

The ML67Q5260 is a single chip LSI that executes fingerprint authentication without external memory by using the embedded fingerprint authentication accelerator. This fingerprint authentication accelerator uses DFT(Discrete Fourier Transform) based algorithm licensed from Precise Biometrics, and supports AuthenTec's slide sensors and certain touch sensors from several sensor manufacturers. Besides the ML67Q5260 has the secure circuit to protect enrolled fingerprint data from unauthorized access. Thus this LSI helps customers quickly design new products that offer convenient security as far as high performance fingerprint authentication, low cost, small size and high level of security.

FEATURES

- Fingerprint authentication
  - DFT (Discrete Fourier Transform) based algorithm licensed from Precise Biometrics
    This DFT based algorithm achieves a lower FTE (False To Enrollment rate) and a higher authentication accuracy especially when a slide sensor is used, as compared to the minutiae algorithm.
  - Easy-to-use
    The fingerprint authentication is performed by the fingerprint authentication accelerator, which does not ask customers for so complicated control.
  - No external memory
    Customer's application program and up to 45 fingerprint data can be stored in the embedded Flash memory on the ML67Q5260. No external memory is required, when a slide sensor is used.
  - High-speed authentication, besides low power consumption
    The highly optimized fingerprint authentication accelerator achieves high-speed authentication using a low speed clock.
      Authentication : < 0.8 seconds (1:1 authentication)
                      < 1.8 seconds (1:45 authentication)
      Enrollment   : < 2 seconds/finger
  - Applicable fingerprint sensor
      Slide sensor   : AuthenTec AES1751 (128 × 8 pixels)

- CPU
  - 32-bit RISC CPU (ARM7TDMI-S)
  - Little endian format
  - Instruction system: A high-density 32-bit instruction and a 16-bit instruction of high-object efficiency, which is the subset of the 32-bit instruction, can be executed in mixed mode.
  - General-purpose register: 32 bits x 31 registers
  - Built-in barrel shifter (ALU and barrel shift operation can be executed by one instruction)
  - Built-in debugging function (JTAG interface)
    The JTAG interface pin is shared with GPIO.

- Built-in Memories
  - 16 Kbyte working RAM for CPU
  - 128 Kbyte Flash ROM for application program and fingerprint template data, whose erase/rewrite times are maximum 10,000
  - 8 Kbyte Mask ROM for update of program in the Built-in Flash ROM

- Interrupt control
  - 1 FIQ resource
      External : 1
  - 20 IRQ resources
      External : 3, Internal : 17
      7 priority levels for each source

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- DMA controller (DMAC)
  - 2 channels
  - Enable to allocate multiple DMA transfer request sources for each channel.
  - Channel priority: fixed mode/round robin mode
  - DMA transfer mode: cycle steal mode/burst mode
  - DMA request type: software requests/hardware requests
  - Maximum transfer count : 65,536
  - Data transfer size: 8 bits/16 bits/32 bits
  - Transfer request source: CPU, SPI, Synchronous SIO, Smartcard IF

- GPIO
  - 13 bits × 1 channel, 12 bits × 1 channel
  - Enable to setting input mode or output mode for each bit
  - Enable to setting as interruption source for each bit
  - Interruption mode: level/edge and positive logic/negative logic

- Timer
  - 16-bit auto reload timer × 4 channel

- Watch dog timer (WDT)
  - 16-bit timer
  - 8.389 seconds max. (when CPU operating frequency is 32 MHz)
  - Enables generation of interrupt or reset by setting

- SIO (UART)
  - Full-duplex asynchronous mode
  - Built-in baud rate generator

- SPI
  - 2 channels of full-duplex serial peripheral interfaces
  - Operating mode: master mode/slave mode
  - Data transfer size: 8 bits (byte) / 16 bits (word)
  - Built-in 16-byte/16-word FIFO on the transmission side and the reception side
  - Supports DMA transfer (master/slave mode)

- Synchronous SIO (SSIO)
  - clock synchronous serial port × 1 channel
  - Data transfer size : 8 bits (byte)
  - Selectable clock polarity
  - Selectable LSB first or MSB first
  - Operation mode: master mode/slave mode
  - Supports DMAC transfer (in master mode only)

- Smart Card interface (Smartcard IF)
  - ISO UART × 1 channel
  - Built-in 16-byte FIFO
  - Built-in parity error counter in receive mode and transmit mode at automatic retransmission
  - Supports asynchronous protocol of T = 0 and T = 1 according to ISO7816 and EMV
  - Built-in error detection code generation and error detection functions by hardware
  - Supports DMA transfer

- USB2.0 full-speed device
  - Compliant with Universal Serial Bus (USB) 2.0
  - Full speed (12 Mbps) × 1 port.
  - End points: 5 or 6
  - Supports all data transfer types (control transfer, bulk transfer, interrupt transfer, isochronous transfer).
  - Built-in SOP generation and CRC5/16 generation functions
  - Access size to data transfer FIFOs: 8 bits/16 bits/32 bits

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- Random number generator (RANDOM)
  - Generates 8-bit random numbers

- Clock
  - Input clock: 12 MHz (oscillator connected)
  - System clock (CPU operating clock): 32 MHz
    System clock is generated by PLL using 12MHz clock.
  - Output clock: 6/12 MHz for fingerprint sensor

- Power management
  - Power saving mode
    •Individual module clock stop mode:
       Clock operation/stop can be set for each functional block.
    •HALT mode:
       Only CPU clock is stopped.
    •STOP mode:
       All clocks are stopped, and start /stop of internal PLL and oscillator circuit are selectable.

- Package
  - 63-pin WCSP Package (S-UFLGA63-4.03x4.01-0.50-W)

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BLOCK DIAGRAM

Figure 1 Block Diagram

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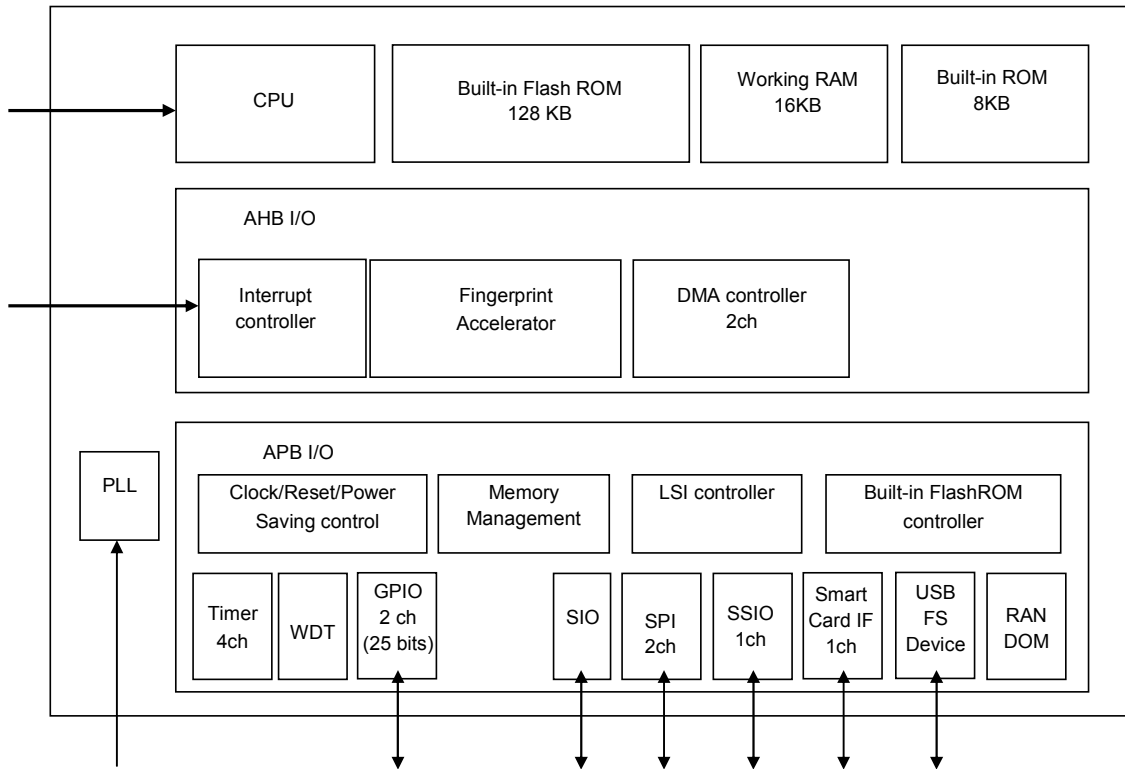
PIN LAYOUT

TESTF	PB01 (SIMVCTL0)	PB03 (SIMVCMD)	PB04 (SIMDATA)	PB06 (SIMCLK)	NTRST	VDDCORE	BSEL1	8
PA08 (SSIOTX)	PB00 (SIMDET)	VDDIO	VDDCORE	PR0	TDO	TCK	VDDIO	7
PA09 (SSIORX)	PA10 (SSIOCLK)	GNDIO	GNDCORE	GNDCORE	TDI	RTCK	GNDIO	6
AFSEL	PUCTL		PB02 (SIMVCTL1)	PB05 (SIMRST)	TMS	PA12 (SIORX)	GNDCORE	5
PB11 (CLKOUT)	GNDCORE	DP	PB08 (EXINT0)	XI	PA07 (SPI1SCK)	PA11 (SIOTX)	VDDCORE	4
VDDCORE	DM	PB09 (EXINT1)	RESETN	XO	PA00 (SPI0MOSI)	PA04 (SPI1MOSI)	PA02 (SPI0SSN)	3
VDDUSB	PB10 (VBUS)	VDDPLL	VDDIO	PA05 (SPI1MISO)	PA03 (SPI0SCK)	VDDIO	PA01 (SPI0MISO)	2
GNDUSB	PB07 (FIQ)	GNDPLL	PA06 (SPI1SSN)	TESTE	GNDIO	VDDCORE	GNDCORE	1
H	G	F	E	D	C	B	A	

S-UFLGA61-4.03x4.01-0.50-W
(Bottom View)

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PIN LIST

Pin No.	Pin name	Primary function			Secondary function			Schmitt	PU/PD(*1)	Drive capacity	5V Tolerant	Initial direction	Initial value
		I/O	Polarity	Description	I/O	Polarity	Description						
D4	XI	I	-	Oscillation Pin	-	-	-	-	-	-	-	I	-
D3	XO	O	-	Oscillation Pin	-	-	-	-	-	-	-	O	-
E3	RESETN	I	N	System Reset	-	-	-	S	PU	-	-	I	-
D7	PR0	I	P	Built-in ROM Port0 (*2)	-	-	-	-	PU	-	-	I	-
B6	RTCK	O	-	JTAG Return Clock	-	-	-	-	-	4mA	-	O	L
B7	TCK	I	-	JTAG Test Clock	-	-	-	-	PU	-	-	I	-
C5	TMS	I	P	JTAG Test Mode State	-	-	-	-	PU	-	-	I	-
C6	TDI	I	-	JTAG Test Data In	-	-	-	-	PU	-	-	I	-
C7	TDO	O	-	JTAG Test Data Out	-	-	-	-	-	4mA	-	O	H
C8	NTRST	I	N	JTAG Test Reset	-	-	-	-	PU	-	-	I	-
B5	PA12	I/O	-	General Purpose Port A12	I	-	SIO Receive Data	-	-	4mA	-	I	-
B4	PA11	I/O	-	General Purpose Port A11	O	-	SIO Transmit Data	-	-	4mA	-	I	-
G6	PA10	I/O	-	General Purpose Port A10	I/O	-	SSIO Communication Clock	-	-	4mA	-	I	-
H6	PA09	I/O	-	General Purpose Port A9	I	-	SSIO Receive Data	-	-	4mA	-	I	-
H7	PA08	I/O	-	General Purpose Port A8	O	-	SSIO Transmit Data	-	-	4mA	-	I	-
C4	PA07	I/O	-	General Purpose Port A7	I/O	-	SPI Clock for CH1	-	-	4mA	-	I	-
E1	PA06	I/O	-	General Purpose Port A6	I	N	SPI Slave Select for CH1	-	-	4mA	-	I	-
D2	PA05	I/O	-	General Purpose Port A5	I/O	-	SPI Data for CH1 (Master Receive / Slave Transmit)	-	-	4mA	-	I	-
B3	PA04	I/O	-	General Purpose Port A4	I/O	-	SPI Data for CH1 (Master Transmit / Slave Receive)	-	-	4mA	-	I	-
C2	PA03	I/O	-	General Purpose Port A3	I/O	-	SPI Clock for CH0	-	-	4mA	-	I	-
A3	PA02	I/O	-	General Purpose Port A2	I	N	SPI Slave Select for CH0	-	-	4mA	-	I	-
A2	PA01	I/O	-	General Purpose Port A1	I/O	-	SPI Data for CH0 (Master Receive / Slave Transmit)	-	-	4mA	-	I	-
C3	PA00	I/O	-	General Purpose Port A0	I/O	-	SPI Data for CH0 (Master Transmit / Slave Receive)	-	-	4mA	-	I	-
H4	PB11	I/O	-	General Purpose Port B11	O	-	Clock Output (for sensor)	-	-	4mA	-	I	-
G2	PB10	I/O	-	General Purpose Port B10	I	-	External Interrupt Input (for USB VBUS)	S	-	4mA	T	I	-
F3	PB09	I/O	-	General Purpose Port B09	I	-	External Interrupt Input (for IRQ 28)	S	-	4mA	-	I	-
E4	PB08	I/O	-	General Purpose Port B08	I	-	External Interrupt Input (for IRQ 30)	S	-	4mA	-	I	-
G1	PB07	I/O	-	General Purpose Port B07	I	-	External Interrupt Input (for FIQ)	S	-	4mA	-	I	-
D8	PB06	I/O	-	General Purpose Port B06	O	-	Smartcard IF Clock	-	-	4mA	-	I	-
D5	PB05	I/O	-	General Purpose Port B05	O	N	Smartcard IF Reset	-	-	4mA	-	I	-
E8	PB04	I/O	-	General Purpose Port B04	I/O	-	Smartcard IF Serial Data	-	-	4mA	-	I	-
F8	PB03	I/O	-	General Purpose Port B03	O	-	Smartcard IF Power Control	-	-	4mA	-	I	-
E5	PB02	I/O	-	General Purpose Port B02	O	-	Smartcard IF Voltage Control 1	-	-	4mA	-	I	-
G8	PB01	I/O	-	General Purpose Port B01	O	-	Smartcard IF Voltage Control 0	-	-	4mA	-	I	-
G7	PB00	I/O	-	General Purpose Port B00	O	-	Smartcard IF Card Detection	-	-	4mA	-	I	-
G3	DM	A	-	USB dev D-	-	-	-	-	-	-	-	I	-
F4	DP	A	-	USB dev D+	-	-	-	-	-	-	-	I	-
G5	PUCTL	O	P	USB dev Pull-up Control	-	-	-	-	-	4mA	-	O	L
H8	TESTF	A	-	FLASH Test Pin	-	-	-	-	-	-	-	A	-
A8	BSEL1	I	P	Boot Device Select 1	-	-	-	-	PD	-	-	I	-
H5	AFSEL	I	P	JTAG Select (ARM/FLASH)	-	-	-	-	PD	-	-	I	-
D1	TESTE	I	P	Test Mode Select	-	-	-	-	PD	-	-	I	-

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Pin No.	Pin name	Description							Schmitt	PU/PD(*1)	Drive capacity	5V Tolerant	Initial direction	Initial value
		Primary function			Secondary function									
		I/O	Polarity	Description	I/O	Polarity	Description							
B8, E7, H3, A4, B1	VDDCORE	-	-	1.8V Power Supply for CORE	-	-	-	-	-	-	-	-	-	-
E6, D6, A5, G4, A1	GNDCORE	-	-	Ground for CORE	-	-	-	-	-	-	-	-	-	-
A7, F7, B2, E2	VDDIO	-	-	3.3V Power Supply for IO	-	-	-	-	-	-	-	-	-	-
A6, F6, C1	GNDIO	-	-	Ground for IO	-	-	-	-	-	-	-	-	-	-
F2	VDDPLL	-	-	1.8V Power Supply for PLL	-	-	-	-	-	-	-	-	-	-
F1	GNDPLL	-	-	Ground for PLL	-	-	-	-	-	-	-	-	-	-
H2	VDDUSB	-	-	3.3V Power Supply for USB	-	-	-	-	-	-	-	-	-	-
H1	GNDUSB	-	-	Ground for PLL	-	-	-	-	-	-	-	-	-	-

*1: PU/PD column:
    PU: Pulled up with a built-in resistor
    PD: Pulled down with a built-in resistor
*2: This pin is used in the Built-in ROM for an update function of the Built-in FlashROM.
  For details, see the User's manual for USB firmware update function.

Termination of Pins Not Used

Pin name	Pin termination
DM, DP, PUCTL	Open
PA00-12 PB00-11	Pulled down
TDO, RTCK	Open
TCK, TMS, TDI, NTRST	Pulled up
TESTF	Must be used as open

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ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Condition	Rating	Unit
Digital power supply voltage CORE (1.8 V)	V_{DD_CORE}	—	−0.3 to +2.5	V
PLL power supply voltage (1.8 V)	V_{DD_PLL}			
Digital power supply voltage I/O (3.3 V)	V_{DD_IO}	—	−0.3 to +4.6	
USB power supply voltage I/O (3.3 V)	V_{DD_USB}			
Input voltage (normal buffer)	V_I	—	−0.3 to V_{DD_IO}+0.3	
Input voltage (5 V tolerant)		V_{DD_IO} = 3.0 V to 3.6 V	−0.3 to +6.0	
		V_{DD_IO} < 3.0 V	−0.3 to V_{DD_IO}+0.3	
Output voltage	V_O	—	−0.3 to V_{DD_IO}+0.3	
Input allowable current	I_I	—	−10 to +10	mA
"H" output allowable current	I_{OH}	—	+10	
"L" output allowable current	I_{OL}	—	−10	
Power dissipation	P_D	T_a = 85°C	455	mW
Storage temperature	T_{STG}	—	−50 to 150	°C

GUARANTEED OPERATING RANGES

(GND = 0 V)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Digital power supply voltage (CORE) (*1)		V_{DD_CORE}		1.62	1.8	1.98	V
PLL power supply voltage (*1)		V_{DD_PLL}		1.62	1.8	1.98	
Digital power supply voltage (I/O)		V_{DD_IO}	—	3.0	3.3	3.6	
USB power supply voltage		V_{DD_USB}		3.0	3.3	3.6	
CPU operating frequency		f_{BUSCLK}	—	-	32	-	MHz
Ambient temperature		T_a		−40	25	85	°C
	Flash read	T_{a_fread}		−40	25	85	
	Flash write	T_{a_fwrite}		−40	25	85	
Flash write count		C_{WR}		—	—	10,000	cycle

* 1: Please supply from same power source to both V_{DD_CORE} pins and V_{DD_PLL} pin.

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ELECTRICAL CHARACTERISTICS

DC Characteristics

DC characteristics (Core/IO)

(V_{DD_CORE} = 1.62 to 1.98 V, V_{DD_IO} = 3.0 to 3.6 V, T_a = −40 to +85°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
"H" input voltage	V_{IH}	—	2.0	—	V_{DD_IO} +0.3	V
"L" input voltage	V_{IL}	—	−0.3	—	0.8	
Schmitt trigger input threshold voltage (3.3 V)	V_{T+}	—	—	—	2.0	
	V_{T-}		0.6	—	—	
Schmitt trigger input threshold voltage (5 V tolerant)	V_{T+}	—	—	—	2.0	
	V_{T-}		0.6	—	—	
"H" output voltage	V_{OH}	I_{OH} = −4 mA	2.4	—	—	
"L" output voltage	V_{OL}	I_{OL} = 4 mA	—	—	0.4	
High level input current (*1)	I_{IH}	V_{IH} = V_{DD_IO}	—	—	10	μA
		pull-down	30	—	140	
High level input current (*2)		V_{IH} = V_{DD_IO}	—	—	10	
		V_{IH} = 5.5 V	—	—	30	
Low level input current (*1)	I_{IL}	V_{IL} = 0 V	−10	—	—	
		pull-up	−140	—	−30	
Low level input current (*2)		V_{IL} = 0 V	−10	—	—	
3-state output leakage current	I_{OZH}	V_{OH} = V_{DD_IO}	—	—	10	μA
		pull-down	30	—	140	
	I_{OZL}	V_{OL} = 0 V	−10	—	—	
		pull-up	−140	—	−30	
Supply current (during STOP) (*4)	I_{DDS_CORE}	—	—	80	1500	μA
	I_{DDS_IO}	(*3)	—	4	20	
	I_{DDS_PLL}	—	—	2	10	
Supply current (during operation) (*5)	I_{DDO_CORE}	f_{BUSCLK} = 32.0 MHz	—	50	70	mA
	I_{DDO_IO}	(*3) (*6)	—	5	10	
	I_{DDO_PLL}	—	—	1	3	

*1: Pins other than 5 V tolerant pins
*2: 5 V tolerant pins
*3: Input ports: VDD_IO or 0 V
    Other ports: No load excluding the current flowing in pull-up/pull-down resistors
*4: LSI supply current when going into LSI stop mode by stopping clock oscillation, PLL operation, and random number generator operation and setting USB power-down mode.
*5: The current supplied to the LSI when fingerprint authentication is executed without USB operation under the conditions that the programs are stored in the built-in Flash ROM and no external memory are connected.
*6: Clock pulse is driven to XI clock input pin.

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DC characteristics (USB)

(V_{DD_CORE} = 1.62 to 1.98V, V_{DD_USB} = 3.0 to 3.6V, Ta = −40 to +85°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Differential input sensitivity	V_{DI}	Absolute value of the difference between the DP and DM pins	0.2	—	—	V
Differential common mode range	V_{CM}	Includes VDI range	0.8	—	2.5	V
Single end input threshold voltage	V_{SE}		0.8	—	2.0	V
High level output voltage	V_{OH}	15K W RL is connected to GND	2.8	—	—	V
Low level output voltage	V_{OL}	1.5K W RL to 3.6 V	—	—	0.3	V
Hi-Z state input/output leakage current	I_{LO}	0 V < VIN < 3.3 V	−10	—	10	μA
Driver output resistance	Z_{DRV}	Steady state	28	—	44	Ω

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AC Characteristics

Reset Timing

$(V_{DD\_CORE}$ = 1.62 to 1.98 V, V_{DD_IO} = 3.0 to 3.6 V, T_a = −40 to +85°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reset pulse width	t_{RSTW}	—	6.0	—	—	ms
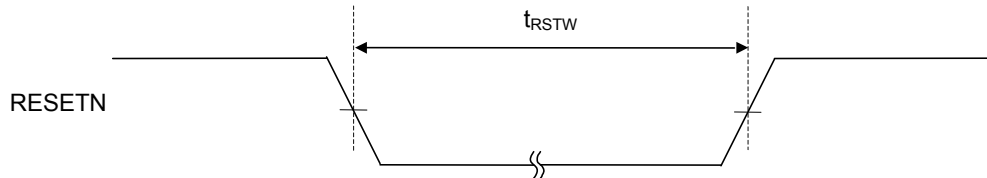
*When power on, release the reset after the clock oscillation stabilization.

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Main Clock Timing

$(V_{DD\_CORE}$ = 1.62 to 1.98 V, V_{DD_IO} = 3.0 to 3.6 V, T_a = –40 to +85°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Main clock (XI/XO) frequency	f_{SYSC}	—	12×0.9975	12	12×1.0025	MHz
Main clock (XI/XO) cycle	t_{SYSC}	—	83.33×0.9975	83.33	83.33×1.0025	ns
Main clock (XI/XO) H pulse width	t_{SYSCH}	—	$0.45 \times t_{SYSC}$	—	$0.55 \times t_{SYSC}$	ns
Main clock (XI/XO) L pulse width	t_{SYSCL}	—	$0.45 \times t_{SYSC}$	—	$0.55 \times t_{SYSC}$	ns
Bus clock frequency (*1)	f_{BUSCLK}	—	—	32	—	MHz
Bus clock cycle (*1)	t_{BUSCLK}	—	—	31.25	—	ns

* 1: Main system bus clock within the LSI and operating clocks of CPU, DMA, etc.

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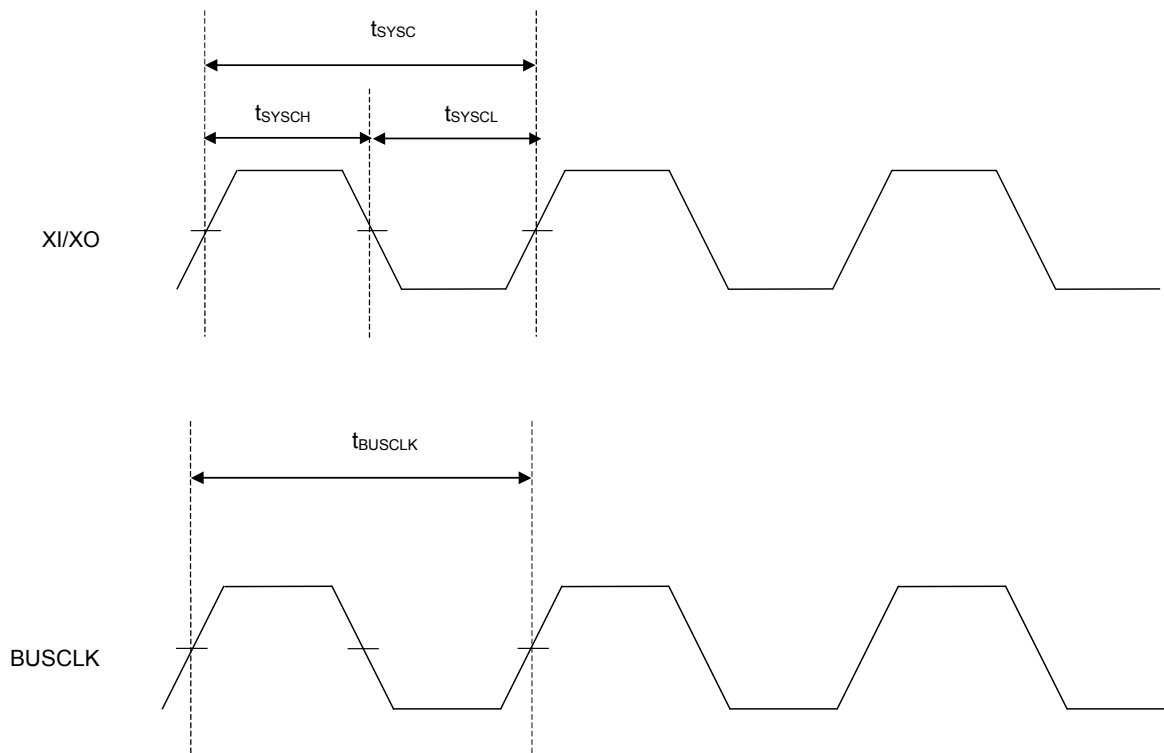
USB Access Timing (Full-Speed)

$(V_{DD\_CORE} = 1.62$ to 1.98 V, $V_{DD\_USB} = 3.0$ to 3.6 V, $T_a = -40$ to $+85°C)$

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	Applied pin
Rise time (*1)	T_R	CL = 50 pF	4	—	20	ns	DP, DM
Fall time (*1)	T_F	CL = 50 pF	4	—	20	ns	
Output signal crossover voltage	V_{CRS}	CL = 50 pF	0.8	—	2.5	V	
Data rate	T_{DRATE}	Average bit rate (12Mbps ±0.25%)	11.97	—	12.03	Mbps	

*1 TR and TF are transition time from 10% to 90% of V_{DD_USB}.

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SPI Access Timing
- Characteristics of master mode timing

(V_{DD_CORE} = 1.62 to 1.98 V, V_{DD_IO} = 3.0 to 3.6 V, T_a = −40 to +85°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Data delay time (output)	t_{DD}		—	—	25	ns
Data setup time (input)	t_{SD}		25	—	—	ns
Data hold time (input)	t_{HD}	CL = 30 pF	0 (*1)	—	—	ns
SPInSSN-SPInSCK lead time	t_{LEAD}		$0.5 * t_{SCK} - 15$	—	$0.5 * t_{SCK} + 15$	ns[*2]
SPInSCK-SPInSSN lag time	t_{LAG}		$0.5 * t_{SCK} - 15$	—	$0.5 * t_{SCK} + 15$	ns[*2]

* 1: Although actual values may become negative depending on the external load, input the serial data so that the data hold time can be guaranteed.
* 2: tSCK is the cycle time of the serial clock for SPI transferring which is obtained by dividing the frequency of the bus clock, whose cycle time is tBUSCLK.

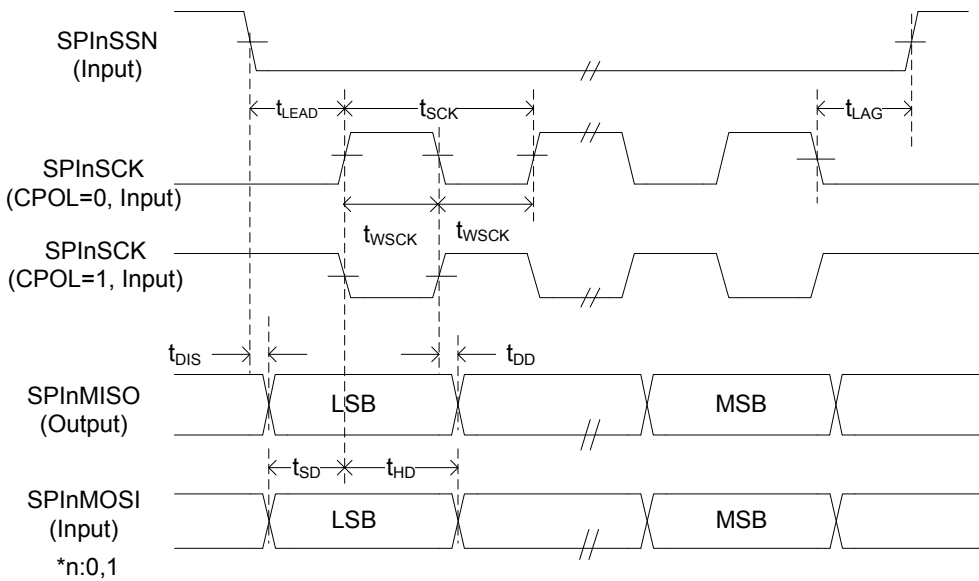SPI master mode timing (CPHA = 0)
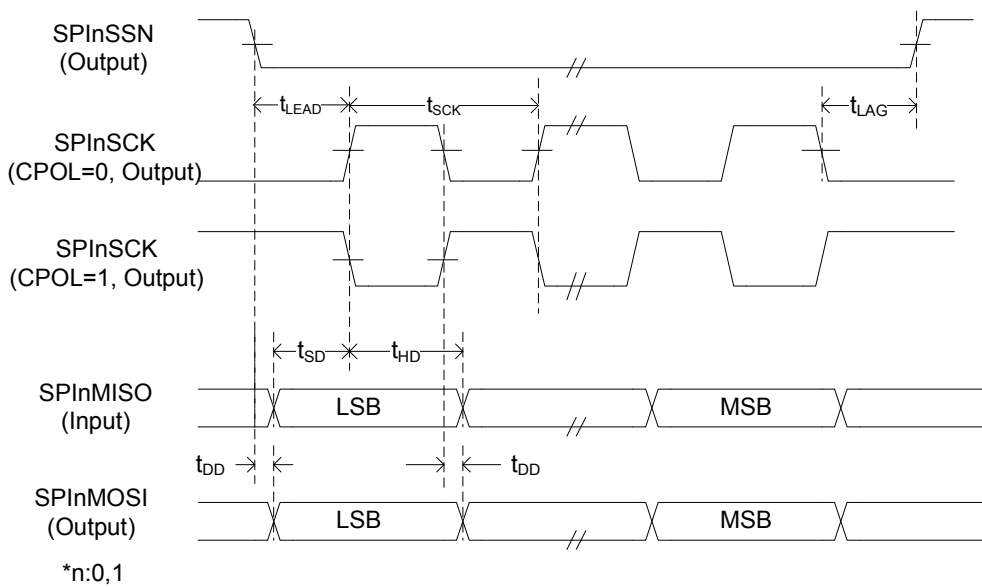
SPI master mode timing (CPHA = 1)

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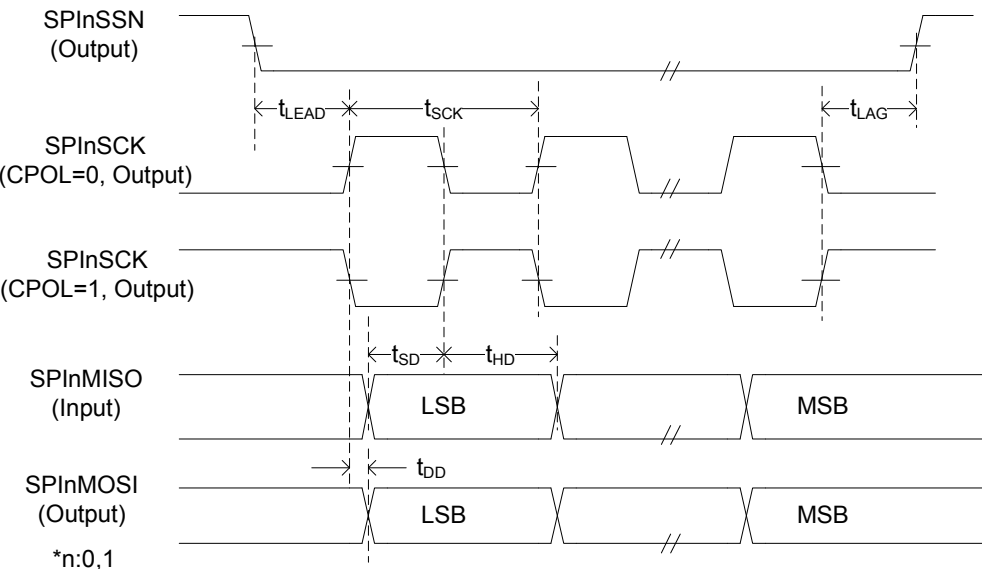
- Characteristics of slave mode timing

$(V_{DD\_CORE} = 1.62$ to 1.98 V, $V_{DD\_IO} = 3.0$ to 3.6 V, $T_a = -40$ to $+85°C)$

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Serial clock cycle time	t_{SCK}		2	—	—	t_{BUSCLK}
Serial clock High/Low time	t_{WSCK}		1	—	—	t_{BUSCLK}
Data delay time (output)	t_{DD}		—	—	25	ns
Data setup time (input)	t_{SD}		25	—	—	ns
Data hold time (input)	t_{HD}	CL = 30 pF	25	—	—	ns
SPInSSN-SPInSCK lead time	t_{LEAD}		25	—	—	ns
SPInSCK-SPInSSN lag time	t_{LAG}		$t_{BUSCLK} + 15$	—	—	ns
Slave data invalid time	t_{DIS}		—	—	25	ns

SPI slave mode timing (CPHA = 0)

SPI slave mode timing (CPHA = 1)
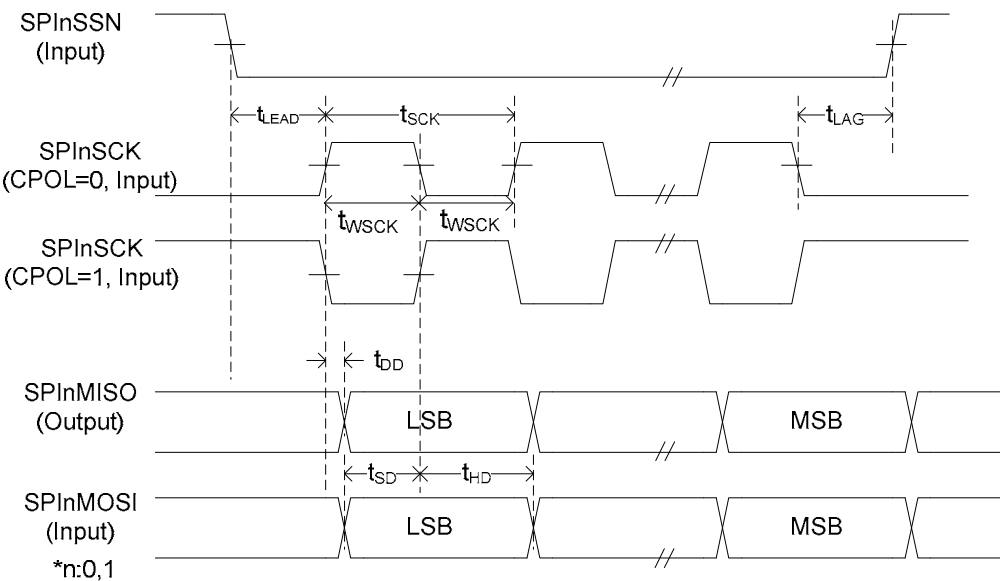
Synchronous SIO Access Timing

Switching between master mode and slave mode can be set for this synchronous SIO by the software register setting. Serial clock polarity can be switched.
When clock polarity is set to positive, data is transmitted (shifted out) on the falling edge of the clock and is received (shifted in) on the rising edge of the clock. At completion of 8-bit data transmission/reception, the clock stops at a high level and the last data is retained for data output.
When clock polarity is set to negative, data is transmitted (shifted out) on the rising edge of the clock and is received (shifted in) on the falling edge of the clock. At completion of 8-bit data transmission/reception, the clock stops at a low level and the last data is retained for data output.
The following waveforms show the cases where the clock polarity is positive.
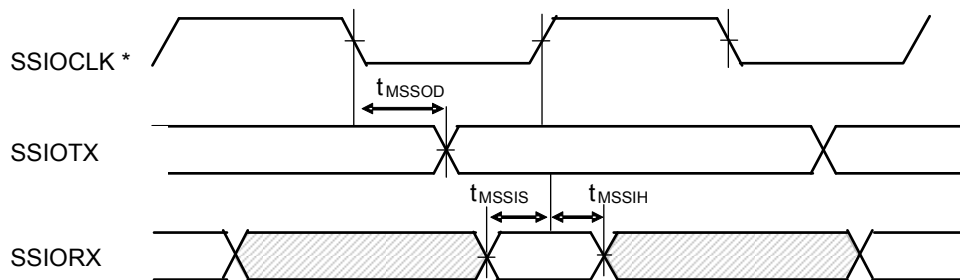
− Master mode

$(V_{DD\_CORE} = 1.62$ to 1.98 V, $V_{DD\_IO} = 3.0$ to 3.6 V, $T_a = -40$ to $+85°C)$

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Output data delay time	t_{MSSOD}		—	—	20	
Input data setting time	t_{MSSIS}	CL = 30 pF	30	—	—	ns
Input data retained time	t_{MSSIH}		10	—	—	

Note:
11 clock outputs for transferring is selectable from 2 synchronous SIO clock sources and the frequency divide ratios.

* Serial clock: Positive polarity

− Slave mode

$(V_{DD\_CORE} = 1.62$ to 1.98 V, $V_{DD\_IO} = 3.0$ to 3.6 V, $T_a = -40$ to $+85°C)$

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Serial clock cycle	T		62.5	—	—	
Output data delay time	t_{SSSOD}	CL = 30 pF	—	—	40	ns
Input data setting time	t_{SSSIS}		20	—	—	
Input data retained time	t_{SSSIH}		20	—	—	

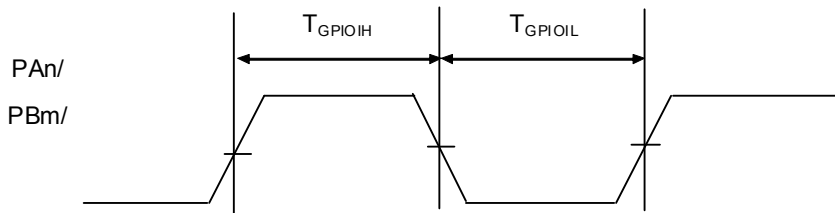* Serial clock: Positive polarity

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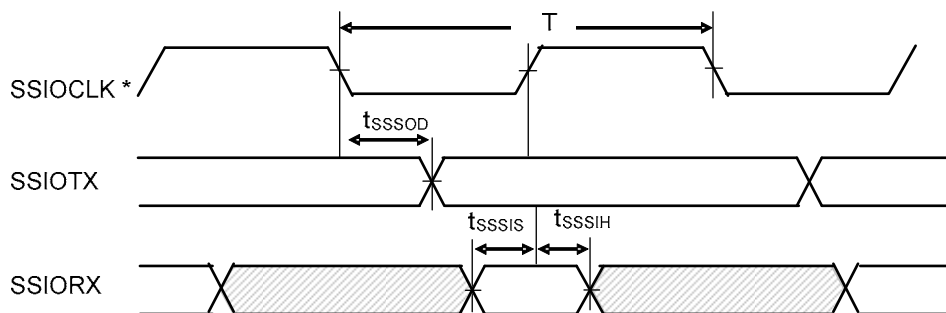
GPIO (PA, PB) Access Timing

$(V_{DD\_CORE} = 1.62 \text{ to } 1.98 \text{ V}, V_{DD\_IO} = 3.0 \text{ to } 3.6 \text{ V}, T_a = -40 \text{ to } +85°C)$

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
PAn, PBm input H duration	T_{GPIOIH}	—	$t_{BUSCLK} \times 2$	—	—	ns
PAn, PBm input L duration	T_{GPIOIL}	—	$t_{BUSCLK} \times 2$	—	—	ns

Note 1: n = 12 to 0, m=11 to 0

○ PAn, PBm input timing (n = 12 to 0, m = 11 to 0)

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Clock Output (Secondary Function of PB11 Pin) Timing

(V_{DD_CORE} = 1.62 to 1.98 V, V_{DD_IO} = 3.0 to 3.6 V, T_a = –40 to +85°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Clock output High duration	t_{CLKOUT_H}	—	45% × t_{CLKOUT}	50% × t_{CLKOUT}	55% × t_{CLKOUT}	ns[*1]
Clock output Low duration	t_{CLKOUT_L}	—	45% × t_{CLKOUT}	50% × t_{CLKOUT}	55% × t_{CLKOUT}	ns[*1]

*t_{CLKOUT} is the cycle time of the 6 MHz or 12 MHz clock generated by 2 clock sources and the frequency divide ratio.
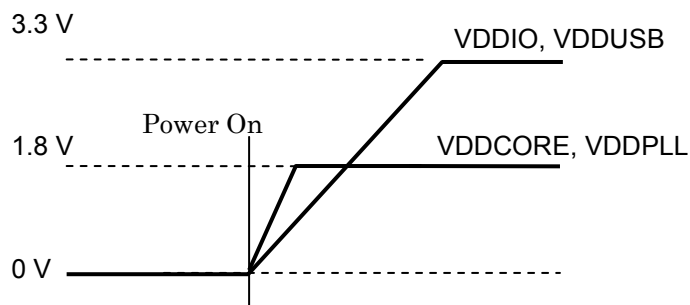
Clock output (secondary function of PB11 pin) timing

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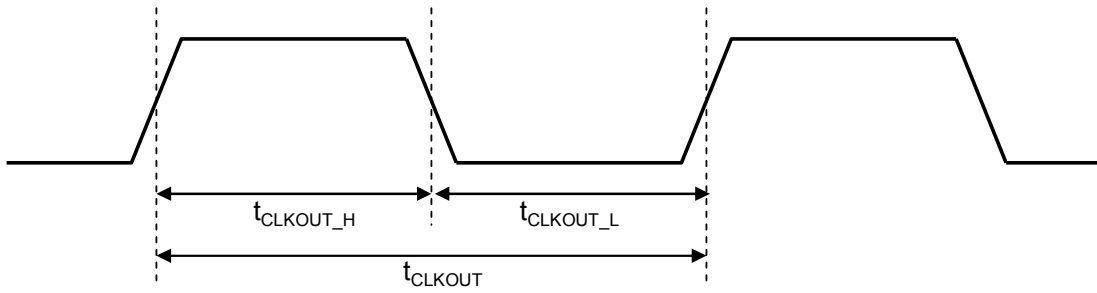
POWER ON / OFF SEQUENCE

Power ON sequence
- Core(VDDCORE,VDDPLL) and IO(VDDIO, VDDUSB) power should be on at the same time, or IO(VDDIO, VDDUSB) power should be on after Core(VDDCORE, VDDPLL) on.
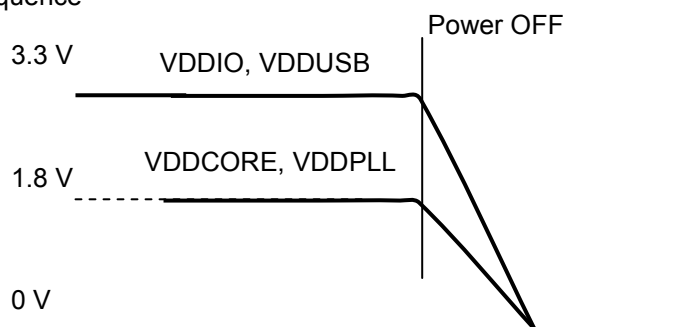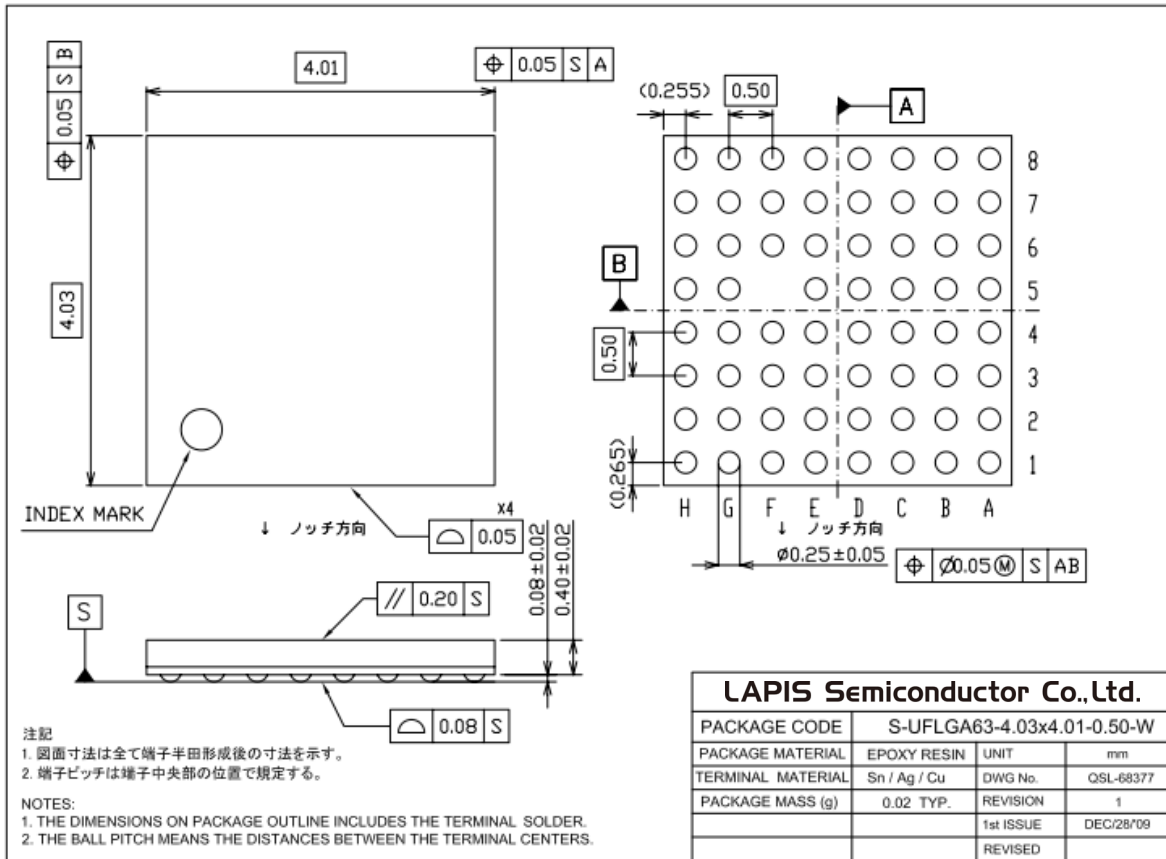
Power ON Sequence

```
3.3 V ------------------------                    VDDIO, VDDUSB

              Power On
1.8 V -------------                               VDDCORE, VDDPLL

0 V  _____ - - - - - - - - - - - - - -
```

Power OFF sequence
- Core(VDDCORE, VDDPLL) and IO(VDDIO, VDDUSB power should be off at the same time, or Core(VDDCORE, VDDPLL) power should be off after IO(VDDIO, VDDUSB) off.

Power OFF Sequence

```
                                  Power OFF
3.3 V  _____ VDDIO, VDDUSB

             VDDCORE, VDDPLL
1.8 V  -----_____

0 V
              - - - - - - - - - - - - - - - - - - -
```

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PACKAGE DIMENSIONS

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PACKAGE CODE	S-UFLGA63-4.03x4.01-0.50-W		
PACKAGE MATERIAL	EPOXY RESIN	UNIT	mm
TERMINAL MATERIAL	Sn / Ag / Cu	DWG No.	QSL-68377
PACKAGE MASS (g)	0.02 TYP.	REVISION	1
		1st ISSUE	DEC/28/'09
		REVISED	

注記
1. 図面寸法は全て端子半田形成後の寸法を示す。
2. 端子ピッチは端子中央部の位置で規定する。

NOTES:
1. THE DIMENSIONS ON PACKAGE OUTLINE INCLUDES THE TERMINAL SOLDER.
2. THE BALL PITCH MEANS THE DISTANCES BETWEEN THE TERMINAL CENTERS.

Notes for Mounting the Surface Mount Type Package

The surface mount type packages are very susceptible to heat in reflow mounting and humidity absorbed in storage. Therefore, before you perform reflow mounting, contact ROHM's responsible sales person for the product name, package name, pin number, package code and desired mounting conditions (reflow method, temperature and times).

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REVISION HISTORY

Document No.	Date	Page Previous Edition	Page Current Edition	Description
PEDL67Q5260-01	Aug.18, 2009	–	–	Preliminary edition 1
PEDL67Q5260-02	Jul.15, 2010	–	–	Preliminary edition 2
FEDL67Q5260-01	Sep.15, 2010	22	22	Final edition 1 - Corrected Power dissipation to 450mW - Changed IIL of Pull-Up pin to -140 - -30uA - Changed IIH of Pull-Down pin to 30 - 140uA
FEDL67Q5260-02	Jul.1, 2011	1	1	Applicable fingerprint sensor AES1711 is deleted.

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